

NCEP60T12A

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP60T12A uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

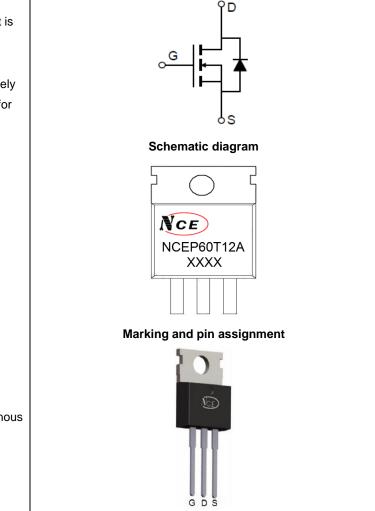
General Features

- $V_{DS} = 60V, I_D = 120A$ $R_{DS(ON)} < 4.0m\Omega @ V_{GS} = 10V$ (Typ:3.5m Ω) $R_{DS(ON)} < 5.0m\Omega @ V_{GS} = 4.5V$ (Typ:4.0m Ω)
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP60T12A	NCEP60T12A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	60	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous (Silicon Limited)	Ι _D	120	А	
Drain Current-Continuous(Tc=100°C)	I _D (100℃)	100	А	
Pulsed Drain Current	I _{DM}	480	А	
Maximum Power Dissipation	PD	180	W	
Derating factor		1.2	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	500	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	







Thermal Characteristic

Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)	····			•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.7	2.4	V
	R _{DS(ON)}	V_{GS} =10V, I _D =60A	-	3.5	4.0	mΩ
Drain-Source On-State Resistance		V_{GS} =4.5V, I _D =60A	-	4.0	5.0	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =60A	40	-	-	S
Dynamic Characteristics (Note4)	····			•		
Input Capacitance	C _{lss}		-	4000	-	PF
Output Capacitance	C _{oss}	$V_{DS}=30V, V_{GS}=0V,$	-	680	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	23	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	tr	V _{DD} =30V,I _D =60A	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =4.7 Ω	-	56	-	nS
Turn-Off Fall Time	tf		-	12	-	nS
Total Gate Charge	Qg		-	67		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=60A,$	-	12		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	8.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =120A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	120	А
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, \ I_F = I_S$	-	48		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	60		nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ C$, V_DD=30V, V_G=10V, L=0.5mH, Rg=25\Omega

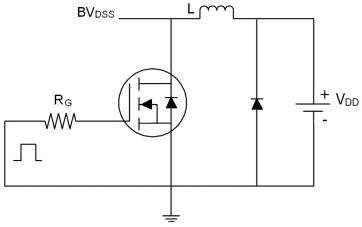


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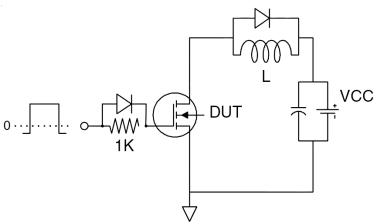




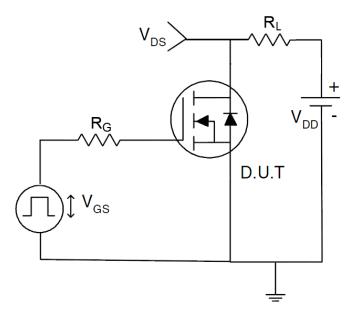
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit

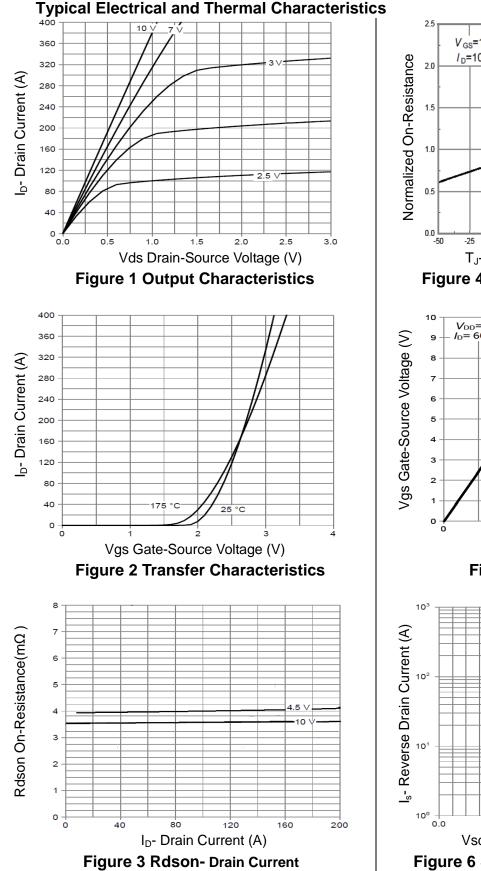


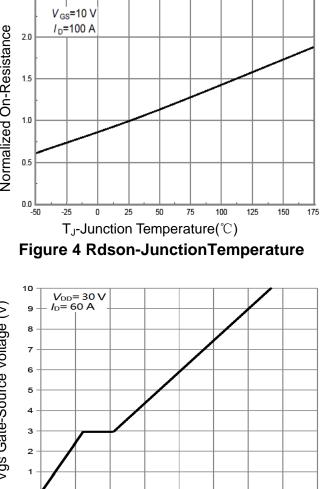


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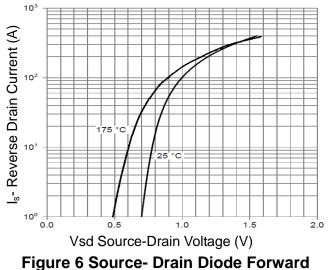


Qg Gate Charge (nC) Figure 5 Gate Charge

40

60

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80



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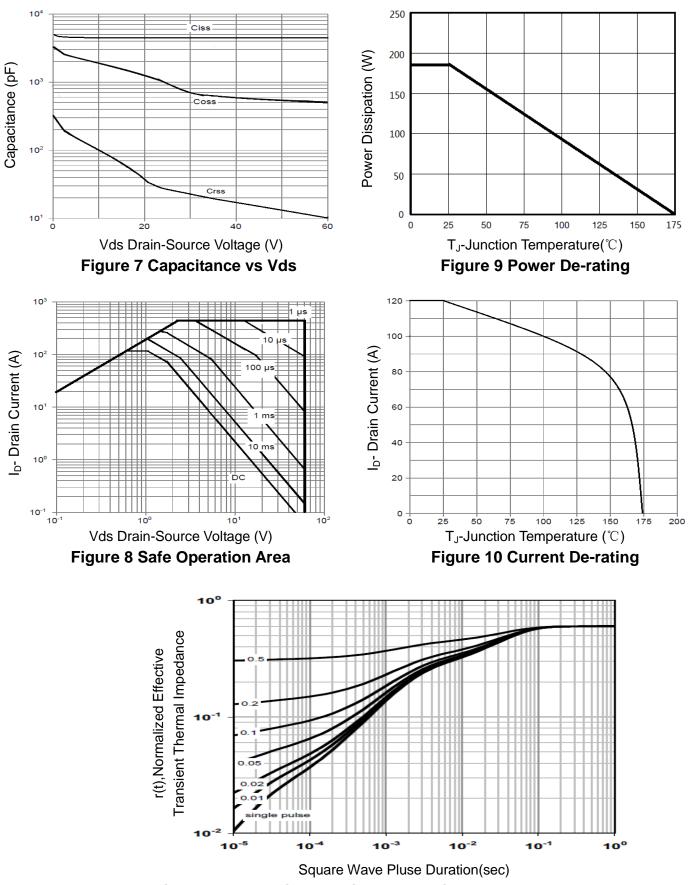


Figure 11 Normalized Maximum Transient Thermal Impedance

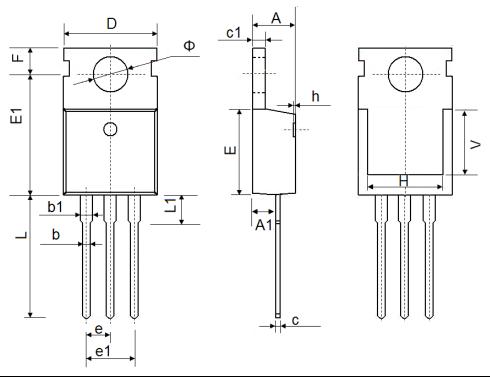


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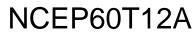
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	







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